

What is claimed is:

1. An electro-optical device comprising:

an active matrix circuit; and

peripheral drive circuits for driving said active matrix circuit, wherein said active matrix circuit and said peripheral drive circuits are provided on a same substrate and surrounded by discharge patterns.

2. A device according to claim 1, wherein a pitch of said discharge patterns is smaller than a pitch of pixels of said active matrix circuit.

3. An active matrix type electro-optical device comprising:

an active matrix circuit arranged on a substrate; and

a capacitor formed adjacent to said active matrix circuit, wherein said capacitor comprising: an electrode formed in the same layer and from the same material as a gate electrode of a thin film transistor arranged in said active matrix circuit; an insulating film made from a

material forming a gate insulating film of the thin film transistor under said electrode of said capacitor; and a semiconductor film constituting an active layer of the thin film transistor under said insulating film of said capacitor.

4. A method for manufacturing an electro-optical device comprising an active matrix circuit and peripheral drive circuits for driving said active matrix circuit, arranged on the same substrate, the method comprising the steps of:

forming a short ring to be connected to all gate lines and all source lines constituting said active matrix circuit;

forming impurity regions for thin film transistors arranged in said active matrix circuit by the implantation of impurity ions; and

forming a capacitor in a region of said short ring by implanting impurity ions into a semiconductor layer under said short ring using said short ring as a mask

simultaneously with the above step of forming impurity regions.

5. A method for manufacturing an active matrix type electro-optical device comprising the steps of:

forming a thin film semiconductor layer under a short ring; and

forming a capacitor using said thin film semiconductor layer.

6. A method for manufacturing an active matrix type electro-optical device comprising the step of forming a capacitor using a thin film semiconductor layer present under a short ring simultaneously with the step of forming impurity regions for thin film transistors arranged in an active matrix circuit.